

33. (As filed) The semiconductor device according to claim 32, wherein the second insulating film is selected from the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

REMARKS

The Examiner has rejected Claims 25-33 under 35 U.S.C. § 103(a) as being obvious over U.S. Patent No. 5,468,684 to Yoshimori et al. (Yoshimori) or U.S. Patent No. 5,192,697 to Leong (Leong). Applicants have amended Claim 25 to include boron as the impurity in the first insulating film of the passivation film.

Yoshimori discloses a semiconductor device which includes a capping layer (95) which is a *phosphorous* doped SOG layer. Yoshimori also discloses an interlayer insulating film (77) which includes a SOG (77E) layer with a silicon dioxide layer (77C) located beneath the SOG layer. Leong discloses a semiconductor device with a sandwich insulating film including a SOG layer containing *argon or arsenic* impurities.

While Yoshimori and Leong disclose an insulating layer comprising a SOG layer and an insulating layer located above and/or beneath the SOG layer, neither reference discloses a *passivation* film including a first insulating film that contains a *boron* impurity.

Based upon the foregoing, Applicants believe that all pending claims are in condition for allowance and such disposition is respectfully requested. In the event that a telephone conversation would further prosecution and/or expedite allowance, the Examiner is invited to contact the undersigned.

Respectfully submitted,

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